

Electronic Supplementary Information

Isoindigo-Based Low Bandgap Conjugated Polymer for *o*-Xylene Processed Efficient Polymer Solar Cells with Thick Active Layers

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Fig. S1 Photos of the solutions of P(1FIID-BT) and P(IID-BT) (5 mg/mL) in *o*-xylene prepared at 80 °C after stored at room temperature for 3 hours.. TGA and DSC curves of P(1FIID-BT) and P(IID-BT).

Table S1. Molecular Weight and Solubility of P(1FIID-BT) and P(IID-BT).

Fig. S2 Solution and film absorption spectra and film cyclic voltammograms of P(1FIID-BT) and P(IID-BT).

Table S2. Optical and Electrochemical Properties of Polymer

Fig. S3 Output and transfer characteristics of OFETs based on pristine films of P(1FIID-BT).

Table S3. OFET Devices Performance of P(1FIID-BT).

Fig. S4 Out-of-plane and in-plane XRD patterns of P(1FIID-BT) films before and after thermal annealing at 150 °C for 20 min.

Fig. S5 AFM height and phase images of P(1FIID-BT) film before and after annealing at 150 °C.

Fig. S6. *J*-*V* and EQE curves of PSC devices (P(1FIID-BT)/PC₆₁BM = 1:1.5 (w/w)) with a different amount of ODT as additives.

Table S4. Device Performance of Conventional PSCs Based on P(1FIID-BT)/PC₆₁BM (1:1.5) with Different Amount of Additives.

Fig. S7. *J*-*V* and EQE curves of inverted PSC devices with 2% ODT as additives.

Table S5. Device Performance of Inverted PSCs Based on P(1FIID-BT)/PC₆₁BM with Different Weight Ratio.

Fig. S8 *J*-*V* characteristics of hole-only and electron-only devices of P(1FIID-BT)/PC₆₁BM (1:1.8, w/w).

Instruments: ^1H and ^{13}C NMR spectra were recorded on a Bruker AV 400 MHz spectrophotometer with chloroform-d (CDCl_3) as solvent and tetramethylsilane (TMS) as an internal standard. High-temperature gel permeation chromatography (GPC) was performed by using 1,2,4-trichlorobenzene as eluent and polystyrene as standard at 150 °C on a PL-GPC 220 system. UV-Vis absorption spectra were measured on a Shimadzu UV3600 UV-vis-NIR spectrometer. Cyclic voltammetry (CV) measurements were carried out on a CHI660a electrochemical workstation using saturated calomel electrode (SEC) as reference electrode, platinum wire as counter electrode and glassy carbon electrode (diameter of 1 cm) as working electrode. TGA was carried out at a heating rate of 10 °C/min under nitrogen flow on a PerkinElmer TGA7. DSC was performed on a PerkinElmer DSC 7 with a heating/cooling rate of ± 10 °C/min under nitrogen flow. Atomic force microscopy (AFM) measurements were carried out in tapping mode on a SPA400HV instrument with a SPI 3800 controller (Seiko Instruments). Transmission electron microscopy (TEM) images were recorded on a JEM-1011 transmission electron microscope with accelerating voltage of 100 KV and camera length of 160 cm. Thin film XRD were tested on Bruker D8 Discover X-ray diffractometer (out-plane) and Rigaku SmartLab X-ray diffractometer (in-plane) with an incidence angle of 0.2° , Cu $\text{K}\alpha$ as X-ray source ($\lambda = 0.154$ nm), tube voltage of 40 KV and electric current of 200 mA. Two dimensional grazing incidence X-ray diffraction (GIXD) was measured at Shanghai Synchrotron Radiation Facility (SSRF) on beam line BL14B1 ($\lambda = 0.124$ nm) with a MarCCD area detector at incidence angle of 0.16° .

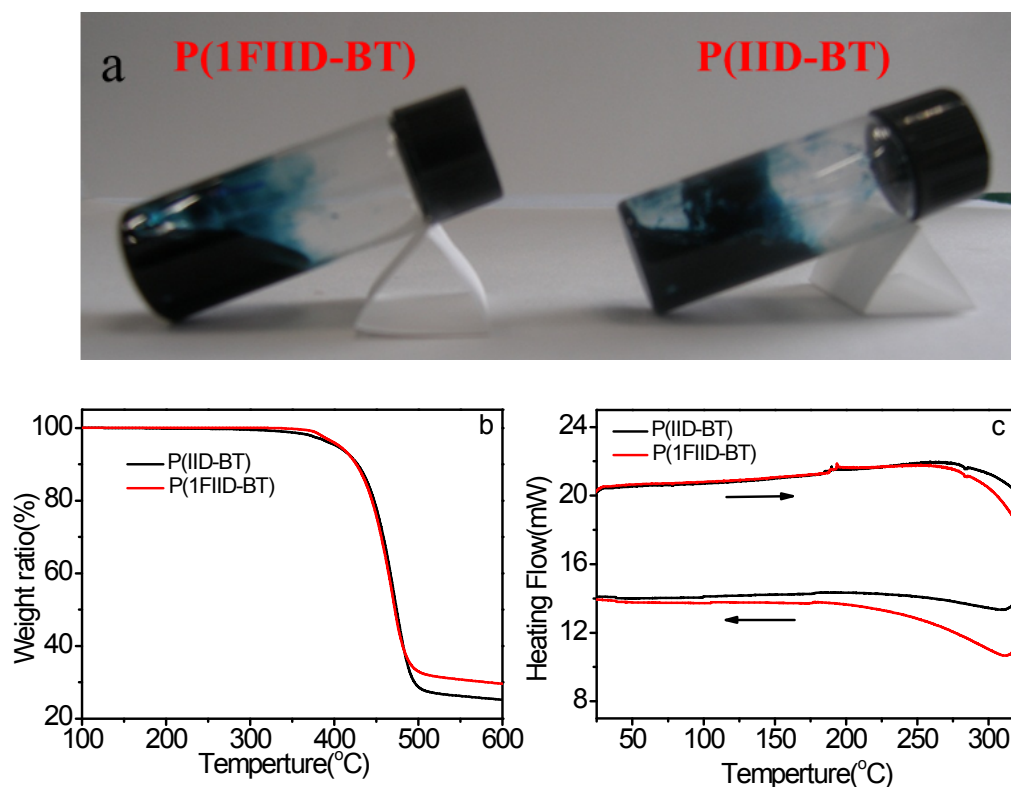


Fig. S1 (a): Photos of the solutions of P(1FIID-BT) and P(IID-BT) (5 mg/mL) in *o*-xylene prepared at 80 °C after stored at room temperature for 3 hours. P(1FIID-BT) solution was stable while P(IID-BT) began to precipitate. TGA (b) and DSC (c) curves of P(1FIID-BT) and P(IID-BT).

Table S1. Molecular Weight and Solubility of P(1FIID-BT) and P(IID-BT).

polymer	M_n [kDa]	M_w [kDa]	\bar{D}	<i>o</i> -DCB ^a	<i>o</i> -xylene ^a
P(IID-BT)	25	82	3.24	S	P
P(1FIID-BT)	65	219	3.36	S	S

^{a)} The concentrations of P(1FIID-BT) and P(IID-BT) were 12 mg/mL in *o*-DCB and 5 mg/mL in *o*-xylene. P: precipitation; S: solution.

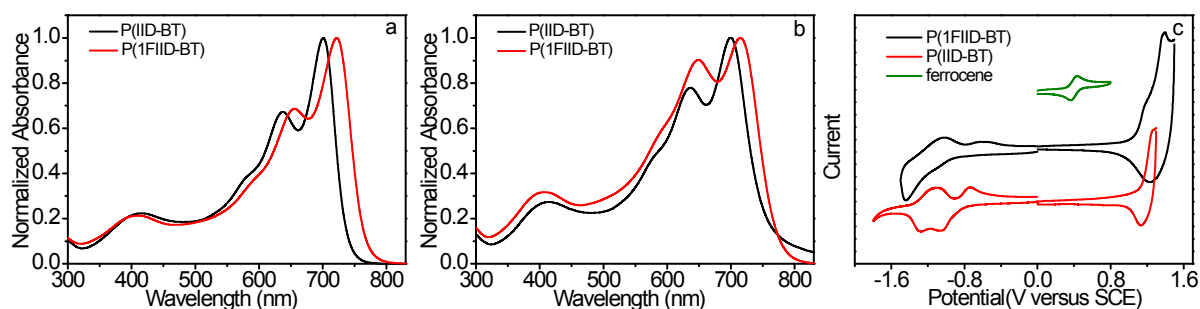


Fig. S2 Solution (a) (1.0×10^{-5} mol/mL in *o*-xylene for P(1FIID-BT) and *o*-DCB for P(IID-BT)) and film (b) absorption spectra and film cyclic voltammograms (c) of P(1FIID-BT) and P(IID-BT).

Table S2. Optical and Electrochemical Properties of Polymers

polymer	UV-vis λ_{max} [nm]		E_g^{opt} [eV]	Cyclic voltammetry			
	Solution	Film		E_{onset}^{ox} [eV]	E_{onset}^{re} [eV]	HOMO [eV]	LUMO [eV]
P(IID-BT)	420/639/701	420/638/701	1.65	0.64	-1.28	-5.44	-3.52
P(1FIID-BT)	412/658/722	410/650/716	1.61	0.66	-1.23	-5.46	-3.57

a) The oxidation and reduction onset potentials of the polymers are versus Fc/Fc⁺.

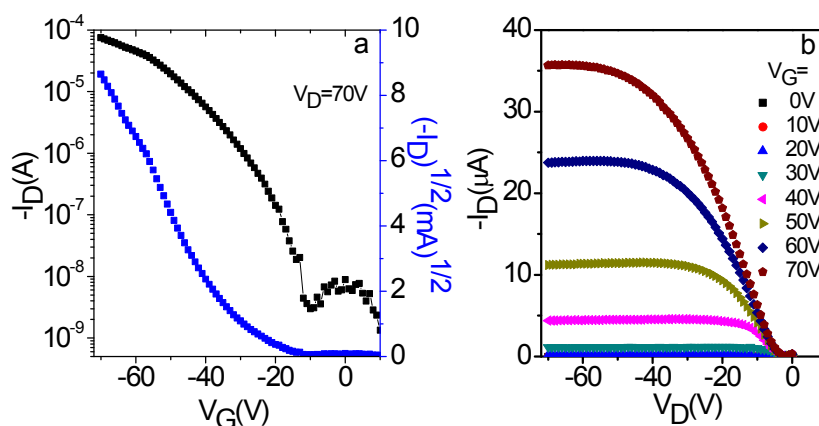


Figure S3. Output (a) and transfer (b) characteristics of OFETs based on pristine films of P(1FIID-BT).

Table S3. OFET Devices Performance of P(1FIID-BT).

$T_{postanneal}$ [°C]	μ_h [cm ² v ⁻¹ s ⁻¹]	V_T [V]	$\text{Log}(I_{on}/I_{off})$
pristine	0.33	-29.8	4-5
150	0.42	-15.5	5-6
200	0.40	-6.4	5-6

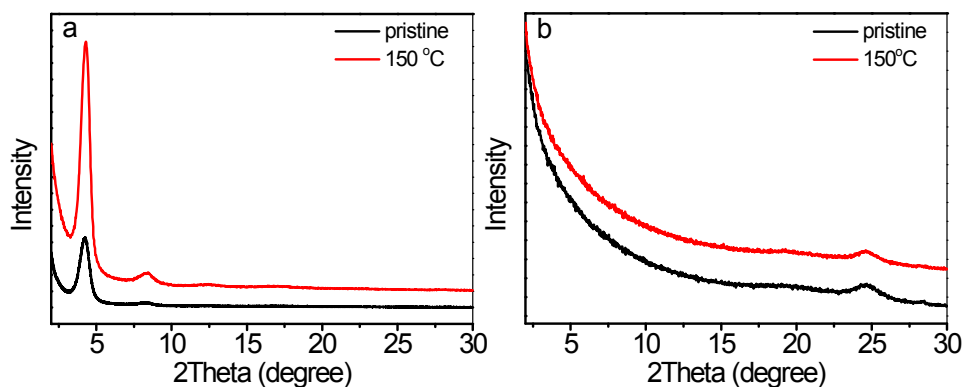


Fig. S4 Out-of-plane (a) and in-plane (b) XRD patterns of P(1FIID-BT) films before and after thermal annealing (150 °C for 20 min).

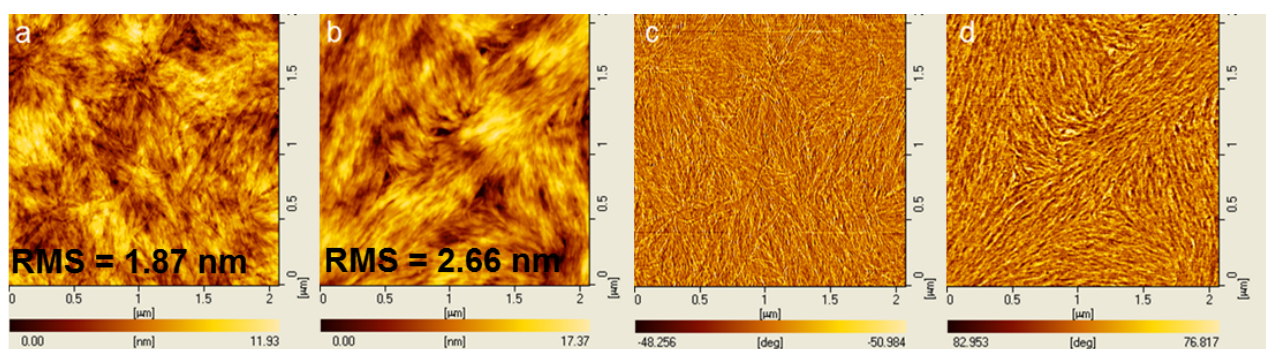


Fig. S5 AFM height (a, b) and phase images (c, d) of P(1FIID-BT) film before (a, c) and after annealing at 150 °C (b, d).

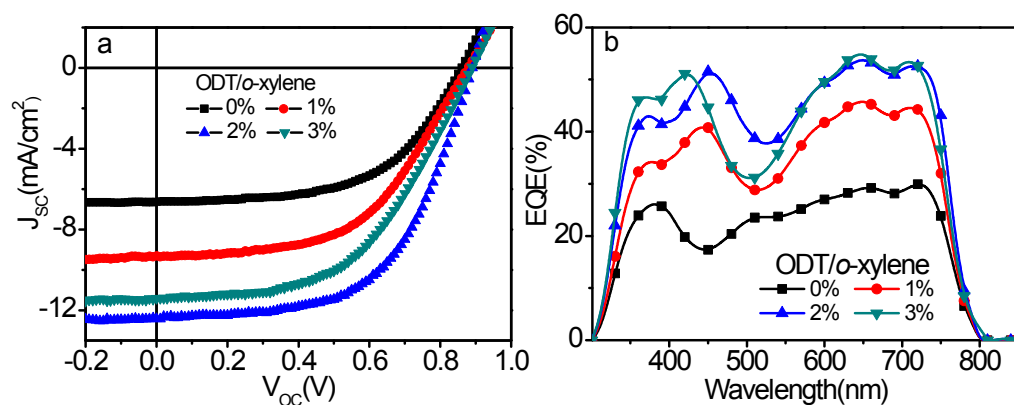


Fig. S6 J-V (a) and EQE (b) curves of PSC devices (P(1FIID-BT)/PC₆₁BM = 1:1.5 (w/w)) with a different amount of ODT as additives.

Table S4. Device Performance of Conventional PSCs Based on P(1FIID-BT)/PC₆₁BM (1:1.5) with Different Amount of Additives.

ODT [%]	V _{oc} [V]	J _{sc} ^a [mA cm ⁻²]	FF	PCE ^b [%]
0	0.86	6.63(6.36)	0.56	3.19(3.16)
1	0.88	9.30(9.61)	0.53	4.33(4.31)
2	0.89	12.41(11.82)	0.57	6.29(6.00)
3	0.89	11.41(11.35)	0.52	5.28(5.15)

a) The values in parentheses are calculated from EQE. b) The values in parentheses are the average of 4 devices.

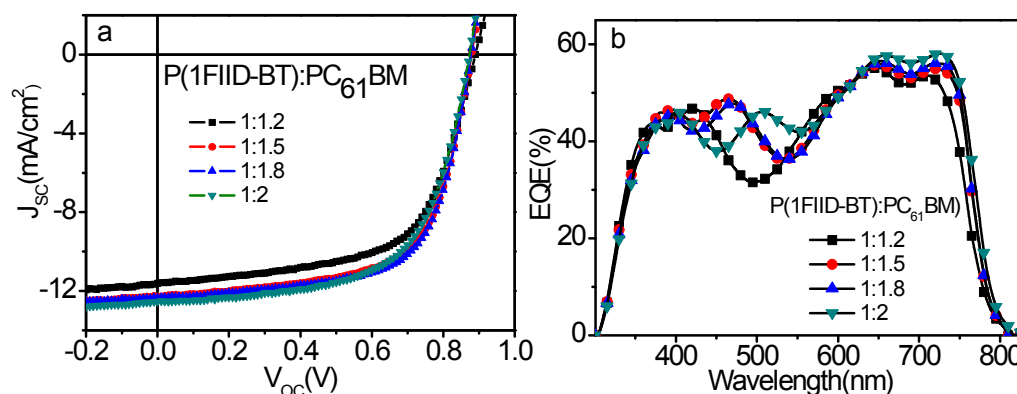


Fig. S7 *J*-*V* (a) and EQE (b) curves of inverted PSC devices with 2% ODT as additives.

Table S5. Device Performance of Inverted PSCs Based on P(1FIID-BT)/PC₆₁BM with Different Weight Ratio.^a

P(1FIID-BT): PC ₆₁ BM	ODT [%]	V _{oc} [V]	J _{sc} ^b [mA cm ⁻²]	FF	PCE ^c [%]
1:1.2	2	0.89	11.61(11.36)	0.62	6.40(6.27)
1:1.5		0.88	12.28(12.09)	0.64	6.92(6.81)
1:1.8		0.88	12.36(12.08)	0.65	7.07(6.91)
1:2		0.87	12.55(12.46)	0.63	6.87(6.83)

a) 2 V% DOT was used as additives. b) The values in parentheses were calculated from EQE. c) The values in parentheses are the average of 4 devices.

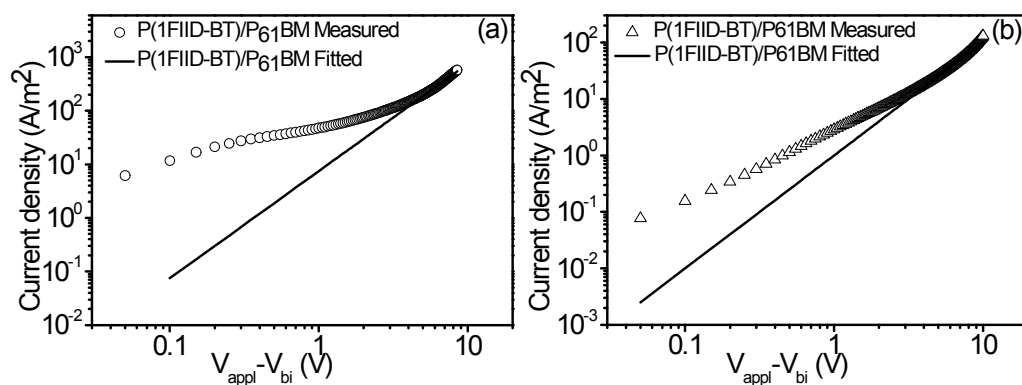


Fig. S8 *J-V* characteristics of hole-only (a) and electron-only (b) devices of P(1FIID-BT)/PC₆₁BM (1:1.8, w/w). Lines represent the fitting results using a model of single-carrier space-charge-limited current with field-dependent mobility. Film thickness was ca. 300 nm.